



Vishay Semiconductors

# Phase Control Thyristors (Hockey PUK Version), 1745 A



K-PUK (A-24)

PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub> 1745 A					
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V, 1400 V, 1600 V				
$V_{TM}$	1.62 V				
I <sub>GT</sub>	100 mA				
T <sub>J</sub>	-40 °C to +125 °C				
Package	K-PUK (A-24)				
Circuit configuration	Single SCR				

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case K-PUK (A-24)
- High profile hockey PUK
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

### TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		1745	A			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
1		3200	Α			
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C			
	50 Hz	33 500	Δ.			
I <sub>TSM</sub>	60 Hz	35 100	A			
124	50 Hz	5615				
l <sup>2</sup> t	60 Hz	5126	KA-S			
V <sub>DRM</sub> /V <sub>RRM</sub>		800 to 1600	V			
t <sub>q</sub>	Typical	200	μs			
T <sub>J</sub>		-40 to +125	°C			

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS								
TYPE NUMBER	CODE		V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA				
	08	800	900					
VS-ST1230CK	12	1200	1300	100				
V3-311230CK	14	1400	1500	100				
	16	1600	1700					



# VS-ST1230C..K

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ABSOLUTE MAXIMUM RATINGS		1			T	
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	180° condu	ction, half sine v	wave	1745 (700)	Α
at heatsink temperature	'I(AV)	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	3200	
		t = 10 ms	No voltage		33 500	
Maximum peak, one-cycle		t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	35 100	A kA <sup>2</sup> s
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		28 200	
		t = 8.3 ms	reapplied		29 500	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	t = 10 ms	No voltage		5615	
		t = 8.3 ms	reapplied		5126	
		t = 10 ms	100 % V <sub>RRM</sub>		3971	
		t = 8.3 ms	reapplied		3625	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10	ms, no voltage	reapplied	56 150	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.93	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V
Low level value of on-state slope resistance	r <sub>t1</sub>	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.17	<b>~</b> 0
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.16	mΩ
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 4000 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.62	V
Maximum holding current	I <sub>H</sub>	T 0500 1 1 40V 11 1		600	A	
Typical latching current	ΙL	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load			1000	mA

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs			
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1$ A/ $\mu$ s $V_d = 0.67$ % $V_{DRM}$ , $T_J = 25$ °C	1.9				
Typical turn-off time	tq	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, $dI/dt$ = 40 A/ $\mu$ s, $V_R$ = 50 V, $dV/dt$ = 20 V/ $\mu$ s, gate 0 V 100 $\Omega$ , $t_p$ = 500 $\mu$ s	200	μs			

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA



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TRIGGERING							
DADAMETED	SYMBOL	TE	TEGT COMPITIONS		VALUES		
PARAMETER	STIMBUL	'S	ST CONDITIONS	typ.	Max.	UNITS	
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	1	6	w	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	(	3	] vv	
Maximum peak positive gate current	I <sub>GM</sub>			3	.0	Α	
Maximum peak positive gate voltage	+ V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms		0			
Maximum peak negative gate voltage	- V <sub>GM</sub>		·				
	I <sub>GT</sub>	T <sub>J</sub> = -40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units	200	-		
DC gate current required to trigger		T <sub>J</sub> = 25 °C		100	200	mA	
		T <sub>J</sub> = 125 °C		50	-		
		T <sub>J</sub> = -40 °C		1.4	-		
DC gate voltage required to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.1	3.0	V	
		T <sub>J</sub> = 125 °C		0.9	-		
DC gate current not to trigger	$I_{\mathrm{GD}}$		Maximum gate current/	10		mA	
DC gate voltage not to trigger	$V_{GD}$	$T_J = T_J \text{ maximum}$	voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.:	25	V	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	°C		
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150			
Maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation single side cooled	0.042	K/W		
		DC operation double side cooled	0.021			
Maximum thermal resistance,	R <sub>thC-hs</sub>	DC operation single side cooled	0.006	¬ ~~vv		
case to heatsink		DC operation double side cooled	0.003			
Mounting force, ± 10 %			24 500 (2500)	N (kg)		
Approximate weight			425	g		
Case style		See dimensions - link at the end of datasheet K-PUK (A-24)		-24)		

△R <sub>thJC</sub> CONDUCTION							
CONDUCTION ANGLE		OIDAL JCTION			TEST CONDITIONS	UNITS	
	SINGLE SIDE	DOUBLE SIDE					
180°	0.003	0.003	0.002	0.002			
120°	0.004	0.004	0.004	0.004			
90°	0.005	0.005	0.005	0.005	$T_J = T_J$ maximum	K/W	
60°	0.007	0.007	0.007	0.007			
30°	0.012	0.012	0.012	0.012			

#### Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC



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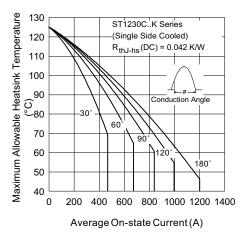


Fig. 1 - Current Ratings Characteristics

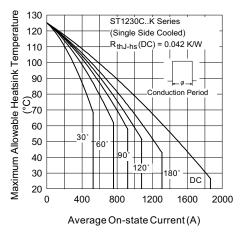


Fig. 2 - Current Ratings Characteristics

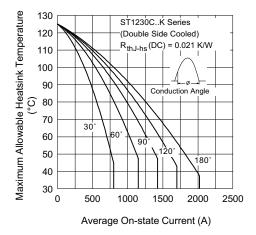


Fig. 3 - Current Ratings Characteristics

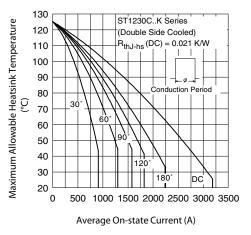


Fig. 4 - Current Ratings Characteristics

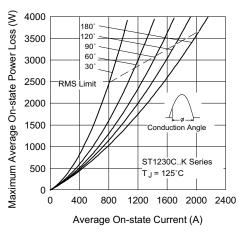


Fig. 5 - On-State Power Loss Characteristics

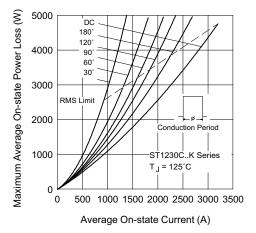
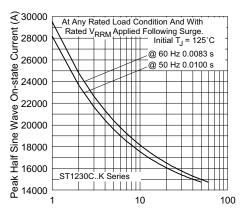


Fig. 6 - On-State Power Loss Characteristics



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Number Of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

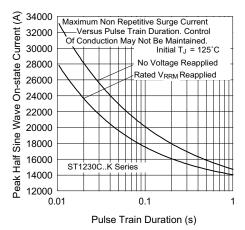


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

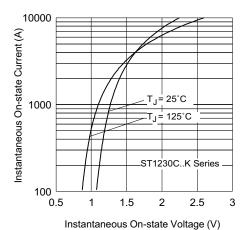


Fig. 9 - On-State Voltage Drop Characteristics

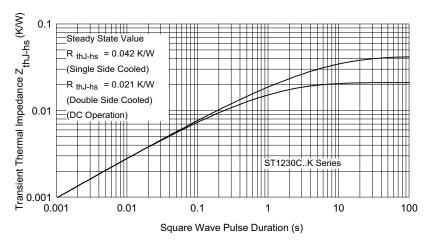


Fig. 10 - Thermal Impedance  $Z_{\text{thJ-hs}}$  Characteristics

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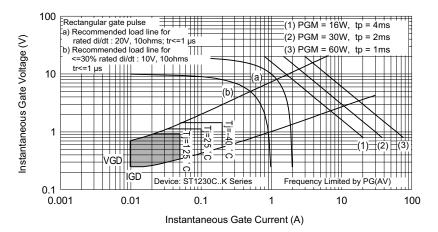
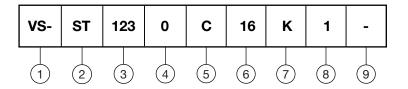


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



- 1 Vishay Semiconductors product
- 2 Thyristor
- 3 Essential part number
- 4 0 = converter grade
- 5 C = ceramic PUK
- 6 Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)
- 7 K = PUK case K-PUK (A-24)
- 8 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)
  - 1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)
  - 2 = eyelet terminals (gate and auxiliary cathode soldered leads)
  - 3 = fast-on terminals (gate and auxiliary cathode soldered leads)
- 9 Critical dV/dt: None = 500 V/µs (standard selection)
  - L = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			

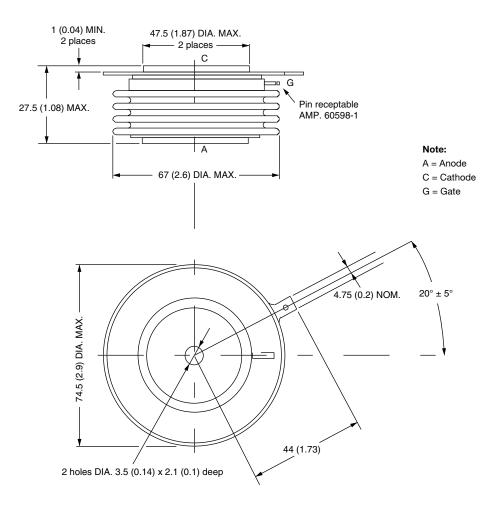


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# K-PUK (A-24)

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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